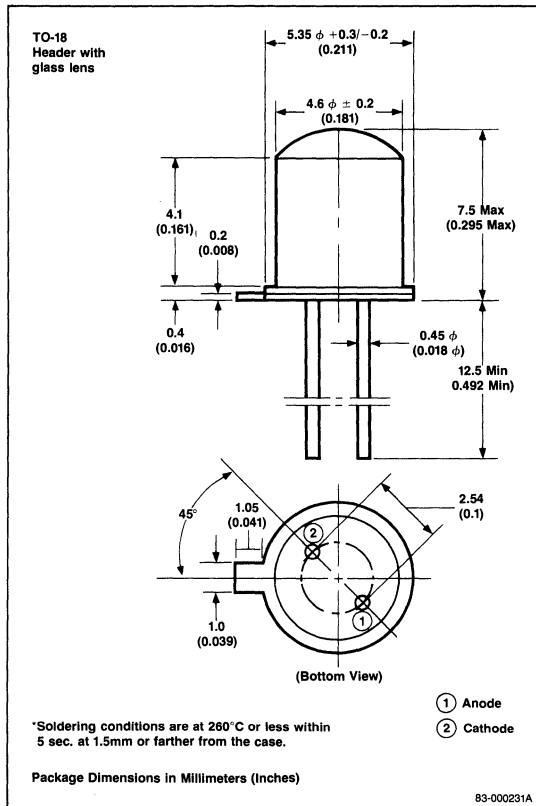


### Description

The SE301A is a GaAs (Gallium Arsenide) infrared emitting diode which is mounted on a TO-18 hermetically sealed header with a glass lens. On forward bias, it emits a spectrally narrow band of radiation peaking at 940nm. The close wavelength match of this device to silicon sensors makes it ideally suited for all source-sense applications. Its low cost and volume producibility opens new areas of use anywhere an infrared source is desirable.

### Package Dimensions



### Features

- Low cost
- High output power — 3mW min
- Fast switching time
- Long life-solid state reliability
- Compact, rugged, lightweight
- Spectrally matched to silicon sensors

### Applications

- Paper tape and punch card readers
- Optical encoders
- Photo choppers
- High speed optoelectronic data links

### Absolute Maximum Ratings

$T_A = +25^\circ\text{C}$

Power Dissipation, $P_D$	150mW
Forward Current, $I_F$	100mA
Peak Forward Current, $I_{PEAK}^1$	1000mA
Reverse Voltage, $V_R$	5.0V
Junction Temperature, $T_J$	+125°C
Storage Temperature, $T_{STG}$	-65°C ~ +125°C

### Electro-Optical Characteristics

$T_A = +25^\circ\text{C}$

Parameters	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Forward Voltage	$V_F$		1.45		V	$I_F = 50\text{mA}$
Pulse Forward Voltage	$V_F$		5.0		V	$I_F = 1.0\text{A}$
Capacitance	C		100		pF	$V = 0$ , $f = 1.0\text{MHz}$
Peak Emission Wavelength	$\lambda_{PEAK}$		940		nm	$I_F = 50\text{mA}$
Spectral Line Half Width	$\Delta\lambda$		60		nm	$I_F = 50\text{mA}$
Output Power	$P_O$	3.0			mW	$I_F = 50\text{mA}$
Peak Output Power	$P_{PEAK}^1$	15			mW	$I_F = 1.0\text{mA}$
Light Turn-On and Turn-Off	$t_{ON}, t_{OFF}$		1		$\mu\text{s}$	

Note: 1.  $f = 1.0\text{kHz}$ , duty cycle 1%.

Typical Characteristics (cont)

T<sub>A</sub> = +25°C

